

## PROFILE

**Name: Dr. Dipok Saikia, M. Sc., M. Phil., Ph. D.**

**Designation: Assistant Professor**

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**Research Area: Organic Electronics, Material science & device development**



Citation indices	
Total Citations	52
h-index	4
i10-index	3

### **\*Research Publications**

[1] **D. Saikia** and P. K. Saikia, "Improved Pentacene Double-Layer Technique to Increase the Air Stability of Pentacene Based Organic Thin-Film Transistors" *IEEE Transactions On Device And Materials Reliability*(U.S.A) 16, 272-274(2016) (**Impact Factor: 1.8**)

[2] R. Sarma and **D. Saikia**, "Low cost MoO<sub>3</sub>/Al bi-layer electrode for Pentacene based OTFTs" *IEEE Electron Device Letters*,(U.S.A.)32( 2)209-211(2011) (**Impact Factor: 2.8**)

[3] **D. Saikia** and P. K. Saikia,"Organic TFTs using Iodine treated pentacene film with High-kdielectric Nd<sub>2</sub>O<sub>3</sub>"*Electro Chemical Society(ECS) Solid State Letters (U.S.A.)4 (11) Q51-Q54 (2015) (Impact Factor: 1.162)*

[4] D. Saikia and P. K. Saikia, "Enhancing air stability of pentacene-based OTFTs with pentacene double layer" *Phys. Status Solidi A (Germany)* 210(11) 2391–2394 (2013) (**Impact Factor: 1.65**)

[5] P.Gogoi, R. Saikia, **D. Saikia**, R.P. Dutta, and S. Changmai, "ZnO TFTs prepared by chemical bath deposition technique with highkLa2O3 gate dielectric annealed in ambient atmosphere" *Physica Status Solidi A (Germany)*, 212, 826–830, (2015) (**Impact Factor: 1.65**)

[6] R Sarma, **D Saikia**, P. Saikia, P.K.Saikia, and B.Baishya, "Pentacene based Thin Film Transistors with High-k Dielectric Nd<sub>2</sub>O<sub>3</sub> as a Gate Insulator" *Brazilian Journal of Physics*, 40( 3), 357-360, (2010) (**Impact Factor: 1.1**)

[7] R Sarma, **D Saikia**, K Konwar and B. Baishya, "Pentacene thin film transistors using La<sub>2</sub>O<sub>3</sub> as gate insulator"*Indian J. Phys.* 84 (5), 547-552, (2010)(**Impact Factor: 1.337**)

[8] P. K. Saikia , P. Saikia, R. Sarma and D. Saikia, *Chiang Mai J. Sci.* 38(4) (2011) 653-657 (**Impact Factor: 0.4**)

[9] P. K. Saikia, U.J. Mahanta, P. Saikia, B. Baishya , R. Sarma, and D. Saikia, "Low threshold voltage pentacene OTFTs with La2O3 gate insulating layer using TSD" *Chiang Mai J. Sci.* 39(2) (2012) 263-269 (**Impact Factor: 0.4**)

[10] R Sarma, D Saikia "Study of tetracene thin film transistors using La2O3 as gate insulator" *Indian J of pure and Appl. Phy.* 47, 876-879, (2009) (**Impact Factor: 0.8**)

### **\*Workshops, Seminars Participated and paper presented**

[1] Paper presented in Indo-Russian Workshop on Nanotechnology and Laser Induced Plasma Proceedings (IRNANO) Year-2009

[2] Participated in a National Workshop on Research Methodology & SPSS *Organized by*, Sibsagar College, Joysagar, Year-2011

[3] Paper presented in National seminar on Recent Development In natural Science on 21st and 22nd January 2012 organized by DKD College, Assam.

[4] Participated in a National thematic workshop on advances in Nanostructured Materials: Application and Perspectives (ANMAP), 2016 Organized by Kaziranga University, Jorhat.

[5] Participated in a International Seminar and Workshop on “Energy, Sustainability and Development”, 12th-14th October, 2012, organized by Department of Physics, Sibsagar College, Joysagar, Assam.

### **\*Working as a reviewer with the following Journals**

1. *Physica Status Solidi A*( Germany)
2. *PSS Rapid Research Letters*( Germany)
3. *IEEE Transactions On Device And Materials Reliability*(U.S.A)

### **\*Research Project**

Principal Investigator in a U.G.C. , India Sponsored Project, Grant No. F.5-75/2013-14/(MRP/NERO)/300

### **Experiences:**

Teaching Experience: 7 years

Research experience: 9 years